

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L119	60885	TFT or "thin film transistor"	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB	2004/05/11 19:52
2	BRS	L120	195609	substrate or wafer	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB	2004/05/11 19:52
3	BRS	L121	1726	(polyphenylene near2 polyimide) or (poly-phenylene near2 polyimide)	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB	2004/05/11 19:52
4	BRS	L125	727	upilex-s or upilex-vt or upilex-50ss or "UBE America"	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB	2004/05/11 19:52
5	IS&R	L127	994	(438/149).CCLS.	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB	2004/05/11 19:52

	Typ	L #	Hits	Search Text	DBs	Tim Stamp
6	IS&R	L129	304	(438/155).CCLS.	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB	2004/05/11 19:52
7	BRS	L131	315	(substrate base wafer bulk) with (polyphenylene near3. polyimide\$2)	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB	2004/05/11 19:52
8	BRS	L133	875	(substrate base wafer bulk) with (polyphenylene and. polyimide\$2)	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB	2004/05/11 19:53
9	BRS	L122	2	((substrate or wafer) near4 ((polyphenylene near2 polyimide) or (poly-phenylene near2 polyimide))) and (TFT or "thin film transistor")	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB	2004/05/11 19:53
10	BRS	L123	28	(substrate or wafer) near4 ((polyphenylene near2 polyimide) or (poly-phenylene near2 polyimide))	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB	2004/05/11 19:53

	Typ	L #	Hits	Search Text	DBs	Time Stamp
11	BRS	L124	18	((polyphenylene near2 polyimide) or (poly-phenylene near2 polyimide)) and (TFT or "thin film transistor")	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB	2004/05/11 19:53
12	BRS	L126	9	(upilex-s or upilex-vt or upilex-50ss or "UBE America") and (TFT or "thin film transistor")	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB	2004/05/11 19:53
13	BRS	L128	2	((438/149).CCLS.) and ((polyphenylene near2 polyimide) or (poly-phenylene near2 polyimide))	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB	2004/05/11 19:53
14	BRS	L130	1	((438/155).CCLS.) and ((polyphenylene near2 polyimide) or (poly-phenylene near2 polyimide))	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB	2004/05/11 19:53
15	BRS	L132	223	((substrate base wafer bulk) with (polyphenylene near3 polyimide\$2)) and (@ad<20000418 @rlad<20000418)	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB	2004/05/11 19:53

	Type	L #	Hits	Search Text	DBs	Tim Stamp
16	BRS	L134	597	((substrate base wafer bulk) with (polyphenylene and polyimide\$2)) and (@ad<20000418 @rlad<20000418)	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/05/11 19:53
17	BRS	L135	152	((substrate base wafer bulk) with (polyphenylene and polyimide\$2)) and (@ad<20000418 @rlad<20000418)) and (chip semiconductor)	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/05/11 19:53.

	Typ	L #	Hits	Search Text	DBs	Tim Stamp
1	BRS	L1	60885	TFT or "thin film transistor"	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/11 10:44
2	BRS	L2	195609 9	substrate or wafer	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/11 10:45
3	BRS	L4	1726	(polyphenylene near2 polyimide) or (poly-phenylene near2 polyimide)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/11 10:45
4	BRS	L6	2	5 and 1	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/11 10:46
5	BRS	L5	28	2 near4 4	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/11 10:49

	Type	L #	Hits	Search Text	DBs	Time Stamp
6	BRS	L7	18	4 and 1	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/11 10:55
7	BRS	L8	727	upilex-s or upilex-vt or upilex-50ss or "UBE America"	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/11 10:55
8	BRS	L9	9	8 and 1	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/11 11:00
9	IS&R	L10	994	(438/149).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/11 11:00
10	BRS	L11	2	10 and 4	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/11 11:03

	Type	L #	Hits	Search Text	DBs	Time Stamp
11	IS&R	L12	304	(438/155).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/11 11:03
12	BRS	L15	1	12 and 4	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/11 11:04

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	60969	TFT or "thin film transistor"	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB	2004/05/13 12:57
2	BRS	L2	195737 3	substrate or wafer	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB	2004/05/13 12:57
3	BRS	L3	1730	(polyphenylene near2 polyimide) or (poly-phenylene near2 polyimide)	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB	2004/05/13 12:57
4	BRS	L4	730	upilex-s or upilex-vt or upilex-50ss or "UBE America"	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB	2004/05/13 12:57
5	IS&R	L5	996	(438/149).CCLS.	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB	2004/05/13 12:57

	Type	L #	Hits	Search Text	DBs	Time Stamp
6	BRS	L6	316	(substrate base wafer bulk) with (polyphenylene near3 polyimide\$2)	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB	2004/05/13 12:57
7	BRS	L7	877	(substrate base wafer bulk) with (polyphenylene and polyimide\$2)	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB	2004/05/13 12:57
8	IS&R	L17	304	(438/155).CCLS.	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB	2004/05/13 12:58
9	BRS	L8	2	((substrate or wafer) near4 ((polyphenylene near2 polyimide) or (poly-phenylene near2 polyimide))) and (TFT or "thin film transistor")	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB	2004/05/13 12:58
10	BRS	L9	28	(substrate or wafer) near4 ((polyphenylene near2 polyimide) or (poly-phenylene near2 polyimide))	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB	2004/05/13 12:58

	Type	L #	Hits	Search Text	DBs	Time Stamp
11	BRS	L10	18	((polyphenylene near2 polyimide) or ((poly-phenylene near2 polyimide)) and (TFT or "thin film transistor"))	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB	2004/05/13 12:58
12	BRS	L11	9	(upilex-s or upilex-vt or upilex-50ss or "UBE America") and (TFT or "thin film transistor")	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB	2004/05/13 12:58
13	BRS	L12	2	((438/149).CCLS.) and ((polyphenylene near2 polyimide) or ((poly-phenylene near2 polyimide)))	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB	2004/05/13 12:58
14	BRS	L13	223	((substrate base wafer bulk) with (polyphenylene near3 polyimide\$2)). and (@ad<20000418 @rlad<20000418)	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB	2004/05/13 12:58
15	BRS	L14	1	((438/155).CCLS.) and ((polyphenylene near2 polyimide) or ((poly-phenylene near2 polyimide)))	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB	2004/05/13 12:58

	Type	L #	Hits	Search Text	DBs	Tim Stamp
16	BRS	L15	597	((substrate base wafer bulk) with (polyphenylene and polyimide\$2)) and (@ad<20000418 @rlad<20000418)	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/05/13 12:58
17	BRS	L16	152	((substrate base wafer bulk), with (polyphenylene and polyimide\$2)) and (@ad<20000418 @rlad<20000418)) and (chip semiconductor)	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/05/13 12:58
18	IS&R	L18	651	(438/30).CCLS.	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/05/13 13:28
19	IS&R	L21	263	(438/152).CCLS.	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/05/13 14:02



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1 Application of engineering plastic materials to office automation and audio-visual appliances in Japan

Yasufuku, S.;

Electrical Insulation Magazine, IEEE , Volume: 8 , Issue: 6 , Nov.-Dec. 1992
Pages:5 - 12

[\[Abstract\]](#) [\[PDF Full-Text \(720 KB\)\]](#) **IEEE JNL**

2 Qualification testing of engineering thermoplastics for electrical distribution applications

Ferrito, S.J.;

Electrical Insulation and Dielectric Phenomena, 2002 Annual Report Conference , 20-24 Oct. 2002
Pages:68 - 71

[\[Abstract\]](#) [\[PDF Full-Text \(386 KB\)\]](#) **IEEE CNF**

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Thin-film transistors on plastic and glass substrates: silicon deposited by microwave plasma ECR-CVD

Lihong Teng Anderson, W.A.

Dept. of Electr. Eng., State Univ. of New York, Buffalo, NY, USA

This paper appears in: **Electron Device Letters, IEEE**

Publication Date: June 2003

On page(s): 399 - 401

Volume: 24 , Issue: 6

ISSN: 0741-3106

Inspec Accession Number: 7701417

Abstract:

Thin-film transistors (TFTs) were fabricated on polyimide and glass substrates at temperatures using microwave ECR-CVD deposited amorphous and nanocrystalline silicon as active layers. The amorphous Si TFT fabricated at 200 °C on the polyimide foil had a saturation region field effect mobility of $4.5 \text{ cm}^2/\text{V}\cdot\text{s}$, a linear mobility of $5.1 \text{ cm}^2/\text{V}\cdot\text{s}$, a threshold voltage of 3.7 V, a subthreshold swing of 0.7 V/decade, and an ON/OFF current ratio of 7.9×10^6 . This large and high ON/OFF current ratio were attributed to the high-quality channel material and less dangling bond defect states. Nanocrystalline Si TFTs fabricated on glass substrates at 400 °C showed a saturation region mobility of $14.1 \text{ cm}^2/\text{V}\cdot\text{s}$, a linear region mobility of $15.3 \text{ cm}^2/\text{V}\cdot\text{s}$, a threshold voltage of 3.6 V, and an ON/OFF current ratio of 6.7×10^6 . TFT performance was mostly independent of substrate type when fabrication conditions were the same.

Index Terms:

amorphous semiconductors carrier mobility dangling bonds elemental semiconductors hydrogen nanostructured materials plasma CVD silicon thin film transistors 200 °C 400 °C ON/OFF current ratio Si:H-SiO₂ TFTs amorphous Si TFT amorphous dangling bond defect states glass substrates high-quality channel materials hydrogen linear region mobility low temperature fabrication microwave plasma ECR-CVD nanocrystalline TFTs nanocrystalline silicon polyimide foil polyimide substrates saturation region mobility silicon deposition subthreshold swing thin-film transistors threshold voltage

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1 DC and microwave noise transient behavior of InP/InGaAs double heterojunction bipolar transistor (DHBT) with polyimide passivation

Yong Zhong Xiong; Geok-Ing Ng; Hong Wang; Fu, J.S.;

Electron Devices, IEEE Transactions on , Volume: 48 , Issue: 10 , Oct. 2001
Pages:2192 - 2197

[\[Abstract\]](#) [\[PDF Full-Text \(144 KB\)\]](#) **IEEE JNL**

2 Current transient in polyimide-passivated InP/InGaAs heterojunction bipolar transistors: systematic experiments and physical model

Hong Wang; Geok-Ing Ng;

Electron Devices, IEEE Transactions on , Volume: 47 , Issue: 12 , Dec. 2000
Pages:2261 - 2269

[\[Abstract\]](#) [\[PDF Full-Text \(172 KB\)\]](#) **IEEE JNL**

3 Polyimide Passivated AlGaN-GaN HFETs With 7.65 W/mm at 18 GHz

Hampson, M.D.; Shen, S.-C.; Schwindt, R.S.; Price, R.K.; Chowdhury, U.; Wu, M.M.; Zhu, T.G.; Yoo, D.; Dupuis, R.D.; Feng, M.;

Electron Device Letters, IEEE , Volume: 25 , Issue: 5 , May 2004
Pages:238 - 240

[\[Abstract\]](#) [\[PDF Full-Text \(120 KB\)\]](#) **IEEE JNL**

4 Electron irradiation effects in polyimide passivated InP/InGaAs single heterojunction bipolar transistors

Shatalov, A.; Subramanian, S.; Chandrasekhar, S.; Dentai, A.; Goodnick, S.M.

Nuclear Science, IEEE Transactions on , Volume: 46 , Issue: 6 , Dec. 1999
Pages:1708 - 1715

[Abstract] [PDF Full-Text (524 KB)] IEEE JNL

5 Amorphous silicon thin-film transistors on compliant polyimide foil substrates

Gleskova, H.; Wagner, S.;

Electron Device Letters, IEEE , Volume: 20 , Issue: 9 , Sept. 1999

Pages:473 - 475

[Abstract] [PDF Full-Text (88 KB)] IEEE JNL

6 Base current transient behavior in polyimide-passivated InP/InGaA heterojunction bipolar transistors

Hong Wang; Geok Ing Ng; McAlister, S.P.;

Indium Phosphide and Related Materials, 2000. Conference Proceedings. 2001

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[Abstract] [PDF Full-Text (260 KB)] IEEE CNF

7 Field-induced instabilities in polyimide passivated lateral PNP trans

El-Kareh, B.; Hook, T.B.; Johnson, M.E.; Lajza, J.J.; McLaughlin, R.W.;

Electronic Components and Technology Conference, 1990. Proceedings., 40th
23 May 1990

Pages:686 - 692 vol.1

[Abstract] [PDF Full-Text (440 KB)] IEEE CNF

8 Thin-film transistors on plastic and glass substrates using silicon deposited by microwave plasma ECR-CVD

Lihong Teng; Anderson, W.A.;

Electron Device Letters, IEEE , Volume: 24 , Issue: 6 , June 2003

Pages:399 - 401

[Abstract] [PDF Full-Text (258 KB)] IEEE JNL

9 Field-induced instabilities in polyimide passivated lateral pnp transi

El-Kareh, B.; Hook, T.B.; Johnson, M.E.; Lajza, J.J.; McLaughlin, R.W.;

Components, Hybrids, and Manufacturing Technology, IEEE Transactions on [also IEEE Trans. on Components, Packaging, and Manufacturing Technology,

A, B, C] , Volume: 13 , Issue: 4 , Dec. 1990

Pages:623 - 628

[Abstract] [PDF Full-Text (456 KB)] IEEE JNL

10 Reduction of base-collector capacitance in InP/InGaAs HBT's using novel double polyimide planarization process

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13 Tri-layer a-Si:H TFTs on polymeric substrates*Thomasson, D.B.; Bonse, M.; Koval, R.J.; Huang, J.R.; Wronski, C.R.; Jackson, T.N.;*

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14 Heterojunction bipolar transistors using GaInAs/InP*Topham, P.J.; Griffith, I.; Riffat, J.; Goodfellow, R.C.;*

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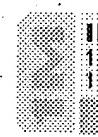
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Garg, A.; Le Coz, Y.L.; Greub, H.J.; McDonald, J.F.; Iverson, R.B.; Interconnect Technology Conference, 1998. Proceedings of the IEEE 1998 International , 1-3 June 1998
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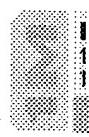
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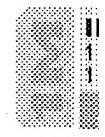
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